

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C
-30V	0.15Ω @ V _{GS} = -10V	-2.6A
-307	0.23Ω @ V _{GS} = -4.5V	-1.5A

Description

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

- Fast Switching Speed
- Low On-Resistance
- Low Threshold
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

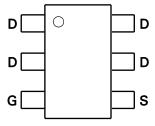
Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.015 grams (Approximate)

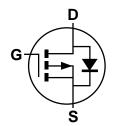




Top View



Pin Out - Top



Equivalent Circuit

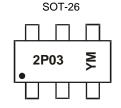
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXM62P03E6TA	2P03	7	8	3,000 Units
ZXM62P03E6TC	2P03	13	8	10,000 Units

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



2P03 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	Е		F	G		Н	ı		J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

CI	naracteristic		Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V _{GS}	±20	V
Continuous Drain Current	V _{GS} = -4.5V	$T_A = +25^{\circ}C \text{ (Note 5)}$ $T_A = +70^{\circ}C \text{ (Note 5)}$	I _D	-1.5 -1.2	А
Pulsed Drain Current (Note 7	7)		I _{DM}	-7.4	Α
Continuous Source Current	(Body Diode)		I _S	-0.54	Α
Pulsed Source Current (Bod	y Diode)		I _{SM}	-7.4	Α

Thermal Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	Б	625	mW
Linear Derating Factor	P_{D}	5	mW/°C
Power Dissipation (Note 6)	Б	806	mW
Linear Derating Factor	P _D	6.4	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	113	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	73	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C

Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
- 6. For a device surface mounted on FR4 PCB measured at t ≤5 seconds.
 7. Repetitive rating pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

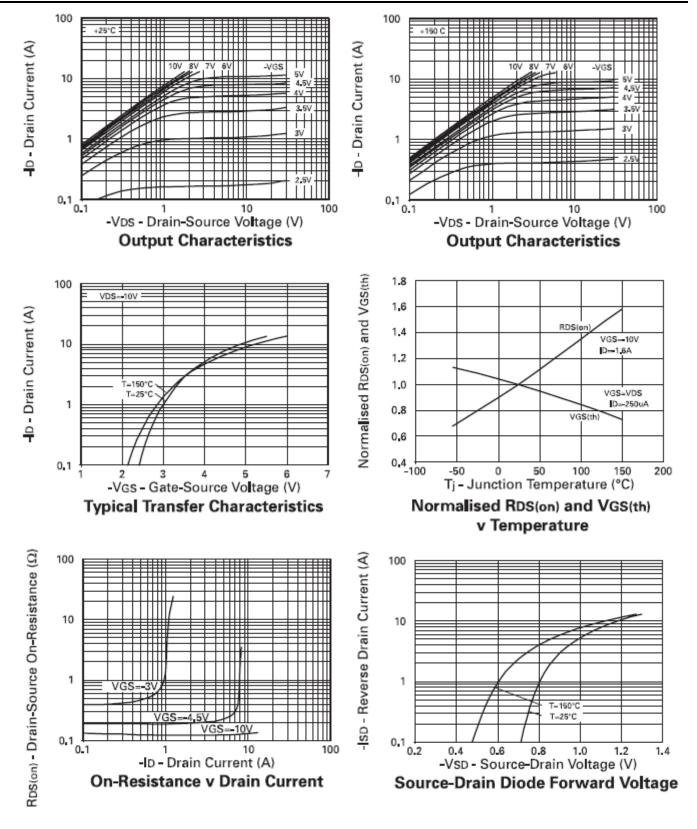
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$I_D = -250\mu A, V_{GS} = 0V$
Zero Gate Voltage Drain Current	I _{DSS}		_	-1	μΑ	$V_{DS} = -30V$, $V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	-1		_	V	$I_D = -250 \mu A, V_{DS} = V_{GS}$
Statio Drain Source On Registence (Note 9)	В			0.15	Ω	$V_{GS} = -10V, I_D = -1.6A$
Static Drain-Source On-Resistance (Note 8)	R _{DS (ON)}	_	_	0.23	77	V _{GS} = -4.5V, I _D = -0.8A
Forward Transconductance (Notes 8 & 10)	g _{fs}	1.1		_	S	$V_{DS} = -10V, I_{D} = -0.8A$
Diode Forward Voltage (Note 8)	V_{SD}			-0.95	V	$T_J = +25$ °C, $I_S = -1.6$ A, $V_{GS} = 0$ V
Reverse Recovery Time (Note 10)	t _{rr}	_	19.9	_	ns	$T_J = +25^{\circ}C$, $I_F = -1.6A$,
Reverse Recovery Charge (Note 10)	Q_{rr}	_	13	_	nC	di/dt = 100A/µs
DYNAMIC CHARACTERISTICS (Note 10)				•		
Input Capacitance	C _{iss}		330	_), OF 1/1/2 OV
Output Capacitance	Coss	_	120	_	pF	$V_{DS} = -25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	45	_		1 = 1:0W112
Turn-On Delay Time (Note 9)	t _{d(on)}		2.8	_		
Turn-On Rise Time (Note 9)	t _r	_	6.4	_	no	V_{DD} = -15V, I_D = -1.6A, $R_G \cong 6.2\Omega$, $R_D \cong 25\Omega$,
Turn-Off Delay Time (Note 9)	t _{d(off)}	_	13.9	_	ns	
Turn-Off Fall Time (Note 9)	t _f	_	10.3	_		
Total Gate Charge (Note 9)	Qg	_	_	10.2		V 04V/ V 40V/
Gate-Source Charge (Note 9)	Q_{gs}			1.5	nC	$V_{DS} = -24V, V_{GS} = -10V,$
Gate-Drain Charge (Note 9)	Q_{gd}	_	_	3		$I_D = -1.6A$

Notes:

- 8. Measured under pulsed conditions. Pulse width = 300 μ s. Duty cycle \leq 2%.
- 9. Switching characteristics are independent of operating junction temperature.
- 10. For design aid only, not subject to production testing.

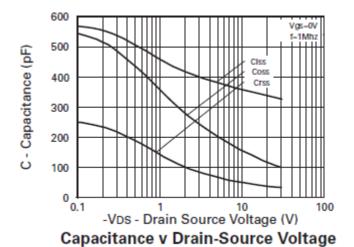


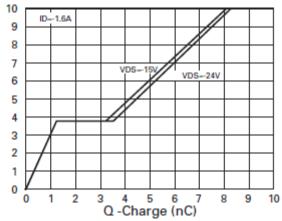
Typical Characteristics





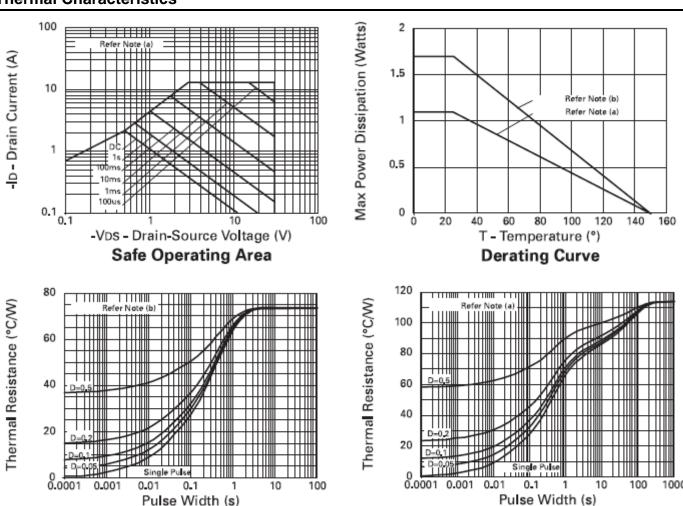
Typical Characteristics (cont.)





Gate-Source Voltage v Gate Charge

Thermal Characteristics



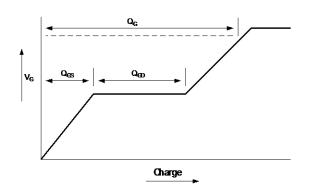
VGS - Gate-Source Voltage (V)

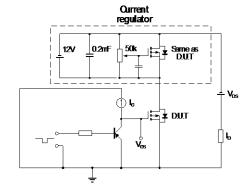
Transient Thermal Impedance

Transient Thermal Impedance



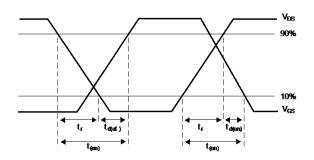
Test Circuits

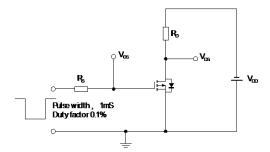




Basic gate charge waveform

Gate charge test circuit





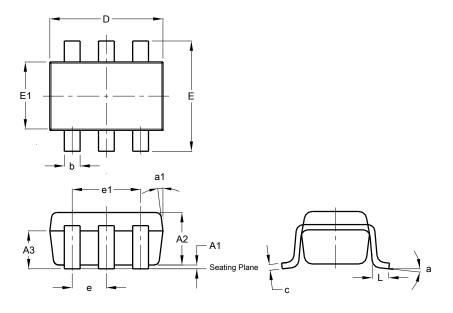
Switching time waveforms

Switching time test circuit



Package Outline Dimensions

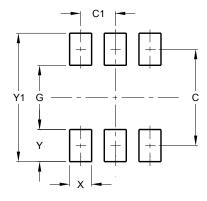
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26						
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	-	-	0.95				
e1	-	-	1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-	1	7°				
All	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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